

IN THE SPECIFICATION

The pending office objected to the disclosure, stating that, "because of the following informalities: The use of "therebetween" on page 9 line 17 of the specification is unclear. Does "therebetween" place the optional TiN layer between layers 16 and 17 or between layers 16 and 42."

Please make the paragraph substitutions indicated in the appendix entitled Clean Version of Amended Specification Paragraphs. The specific changes incorporated in the substitute paragraphs are shown in the following marked-up versions of the original paragraphs.

The paragraph beginning on page 4, line 20 is amended as follows:

Brief Description of the Figures

Figure 1A is a cross-sectional view of a contact hole that has been etched through an insulative layer to an underlying semiconductor substrate.

Figure 1B is a cross-sectional view of the contact hole of Figure 1A, comprising titanium and titanium silicide film.

Figure 2 is a cross-sectional view of the contact hole of Figure 1A, comprising a film of second reducing agent.

Figure 3A is a cross-sectional view of a contact hole as in Figure 1A, including additional structures according to an embodiment of the invention. [the contact hole of Figure 1A, comprising a titanium film.]

Figure 3B is a block diagram of a memory.

The paragraph beginning on page 9, line 9 is amended as follows:

Subsequently, the integrated circuit 19 is annealed at a temperature of between approximately 250 to 750 degrees Celsius. Alternatively, the temperature may range from approximately 250 to 800 degrees Celsius. In one embodiment, the temperature is